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Urbach and dispersion parameters characterization of NiO doped Fe₂O₃ thin films

Sami Salmann Chiad

Department of Physics, College of Education, Al-Mustansiriyah University, Baghdad, (IRAQ)

ABSTRACT

Nickel oxide doped Fe_2O_3 thin films have been prepared by spray pyrolysis technique on glass substrate temperature 400 °C. The initial solution was including a 0.1 M/L for both NiCl₂ and FeCl₃ diluted with redistilled water and a few drops of HCl. The effect of NiO-doping on Urbach energy and dispersion parameters was studied. UV-Visible spectrophotometer in the range of (300-900) nm used to determine absorption spectra. The Urbach energy decreased with increasing NiO content that inversely proportion to the energy gap, which increased from 2.53 eV before doping to 2.88 eV after 3% NiO-doping, also the same behavior of absorbance and the optical conductivity. While the real and imaginary dielectric constants and dispersion parameters such as E_d , E_a , M_{-1} , and M_{-3} are decreased with increasing NiO content in Fe₂O₃ thin films. © 2015 Trade Science Inc. - INDIA

INTRODUCTION

Iron (III) oxide (Fe₂O₃) is a low-cost semiconductor having high stability and can absorb most of the visible light in the solar spectrum. Iron (III) oxide has a band gap of 2.0 to 2.2 eV; therefore, it can absorb solar radiation from 565 to 295 nm, which comprises 38% of the photons of sunlight at AM $1.5^{[1]}$. As one of the main fields of solar energy research concern the development of so-called solar fuels^[2], and considerable attention has been focused on developing new semiconductors for the photoelectron chemical (PEC) conversion^[3-4]. Other applications of Fe₂O₃ such as: catalyst^[5], a magnetic material^[6], a photo catalyst^[7], an anode in Li-ion batteries^[8], in photo electrochemical solar cells^{[9-}

KEYWORDS

Fe₂O₃; NiO; Eurbach energy; Dispersion Parameters.

^{10]}, a water splitter^[11], in non-linear optics^[12], and for gas sensors^[13-14].

Many researchers have worked on different techniques such as, sputtering^[15], and thermal oxidation^[16], ultrasonic spray pyrolysis (USP) and conventional spray pyrolysis (SP)^[17-18], atmospheric pressure chemical vapor deposition (APCVD) method^[19], DC reactive magnetron sputtering^[20], sol– gel method^[21], potentiostatic anodization^[22], as well as sintered disks^[23] and single crystals^[24-25], for fabricating α - Fe₂O₂ photoanodes.

Present work is to study the effect of NiO content (0, 1, and 3%) on Urbach energy and dispersion parameters of NiO:Fe₂O₃ thin films that prepared by chemical spray pyrolysis method.

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EXPERIMENTAL

Thin films of Fe_2O_2 doped by various ratios of NiO have been prepared by chemical pyrolysis technique, this technique is widely used for the largescale production of films owing to its low production cost and simplicity of operation. A laboratory designed glass atomizer was used for spraying the aqueous solution, which has an output nozzle about 1 mm. The films were deposited on preheated cleaned glass substrates at a temperature of 400 °C.A 0.1 M for both NiCl₂ (Sigma Aldrich UK)and FeCl₂(Merck Chemicals Germany)diluted with redistilled water and a few drops of HCl. Volumetric concentration of 1% and 3% was achieved the optimized conditions have been arriving at the following conditions; spray time was 10 s and the spray interval 2min was kept constant, the carrier gas (filtered compressed air) was maintained at a pressure of 105Nm⁻², and distance between nozzle and the substrate was about $30 \text{ cm} \pm 1 \text{ cm}$.

Thickness of the sample was measured using the weighting method and was found to be around 400 nm. Optical transmittance and absorbance were recorded in the wavelength range (300-900nm) using UV-Visible spectrophotometer (Shimadzu Company Japan).

RESULTS AND DISCUSSIONS

The absorption spectrum of NiO:Fe₂O₃ thin films

in the spectral range of (300-900) nm was prepared at substrate temperature of 400 °C and different NiO contain is shown in Figure 1. From this figure, it can show that the spectral characterization is affected by contain of NiO. This result attributed to the creation of levels at the energy band gap, and this leads to the shift of peaks to longer wavelengths. The optical absorption spectrum decreases as the wavelength extends toward the visible region. The absorbance decreases significantly and from (600-900) nm becomes linear.

The real part (ε_1) is associated with the term that how much it will slow down the speed of light in the material and the imaginary part (ε_2) gives that how a dielectric absorb energy from electric field due to dipole motion. The real and imaginary parts of dielectric constant can be related by the following formulas^[26]:

$$\varepsilon_1 = \mathbf{n}^2 \cdot \mathbf{k}^2 \tag{1}$$

$$\mathbf{s}_2 = 2\mathbf{n}\mathbf{k} \tag{2}$$

Where n is the refractive index and k is the extinction coefficient. Figure 2 and Figure 3 are representing the relationship between ε_1 and ε_2 with wavelength. From these figures, it can notice the decreases of ε_1 and ε_2 with increasing NiO contain in NiO:Fe₂O₃ thin films. This decreases more clearly in ε_1 than that of ε_2 .

The absorption coefficient (α) can be used to calculate the optical conductivity as follows^[27]:

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 $Q_{opt} = \frac{\alpha nc}{c}$





Figure 2 : The variation of real part of dielectric constant with wavelength for $NiO:Fe_2O_3$ thin films for deferent contain of NiO



Figure 3 : The variation of imaginary part of dielectric constant with wavelength For $NiO:Fe_2O_3$ thin films for different contain of NiO

Where c is the velocity of light, n is the refractive index, and α is the extinction coefficient. Figure 4 shows the variation of optical conductivity with wavelength. The increased of optical conductivity at low wavelengths is due to the high absorbance of NiO:Fe₂O₃ thin films with different doping and also may be due to the electron excited by photon energy^[28].

The absorption coefficient near the band edge shows an exponential dependence on photon energy^[29]:

$$\alpha(\lambda) = \alpha_0 \exp\left[\frac{hv}{E_{\rm u}}\right] \tag{4}$$

Where E_{U} is the Urbach energy which corresponds to the width of the band tail and can be evaluated as

Physical CHEMISTRY An Indian Journal the width of the localized states, α_0 is a constant, and hv is the photon energy. Thus, a plot of In $[\alpha(\lambda)]$ versus hvshould be linear and Urbach energy can be obtained from the slope that shown in Figure 5. The Urbach energy values are listed in TABLE 1.

Wemple and DiDomenico^[30-31], used a single oscillator dispertion of the frequency-dependent dielectric constant to define "dispersion energy" parameters E_d and E_o . The dispersion plays an important role in the research for optical materials, because it is a significant factor in optical communication and in designing devices for spectral dispersion^[32]. The model describes the dielectric response for transitions below the optical gap. The disper-



Figure 4 : The variation of optical conductivity with wavelength for NiO:Fe2O3 thin films for different contain of NiO



Figure 5 : The variation of lna with photon energy for NiO:Fe₂O₃ thin films for different contain of NiO





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Figure 7 : The variation of $(n^2-1)^{-1}$ with $(1/\lambda^2)$ for NiO:Fe₂O₃ thin films for different contain of NiO TABLE 1 : The optical parameters of NiO:Fe₂O₃ thin films for different content of NiO

Sample	E _d (eV)	E _o (eV)	Eg (eV)	ی3	n(o)	M ₋₁	M ₋₃ (eV ⁻²)	S _o x10 ¹³ (m ⁻²)	λ_o (nm)	U _E (meV)
Pure	50.64	5.06	2.53	11.00	3.32	10.00	0.39	3.35	445	625
1%	33.40	5.34	2.67	7.25	3.69	6.25	0.22	2.77	435	588
3%	28.80	5.77	2.88	6.00	2.45	5.00	0.15	2.76	404	515

 $\mathbf{E}_{o}^{2} = \frac{\mathbf{M}_{-1}}{\mathbf{M}_{-1}}$

sion parameters of the films were determined from the relation given by^[33]:

$$n^{2} = 1 + \frac{E_{o}E_{d}}{E_{o}^{2} - E^{2}}$$
(5)

Where E_o is the single oscillator energy and E_d is the dispersion energy, which is a measure of the intensity of the inter band optical transitions. This model describes the dielectric response for transitions below the optical gap. $(n^{2-1})^{-1}vs$. $(hv)^2$ plots for the NiO:Fe₂O₃ thin films was plotted (see Figure 6). E_o and E_d values were determined from the slope, $(E_oE_d)^{-1}$ and intercept (E_o/E_d) , on the vertical axis. The parameter E_o is an average energy gap and can be related by an empirical formula to the optical band gap value: $E_o=2E_g^{[34]}$. The values of E_o , E_d , and E_o are listed in TABLE 1.

The refractive index (n_x) at infinite wavelength (λ_x) can be determined by the following relation^[35]:

$$\frac{\mathbf{n}_{\infty}^{2}-1}{\mathbf{n}^{2}-1} = 1 - \left(\frac{\lambda_{o}}{\lambda}\right)^{2}$$
(6)

The plot of $(n^2-1)^{-1}$ vs. λ^{-2} was plotted to obtain n_{α} value of NiO:Fe₂O₃ thin film as shown in Figure 7. The moments of the optical spectra M_{-1} and M_{-3} can be obtained from the relationships^[36]:

 $\mathbf{E}_{d}^{2} = \frac{\mathbf{M}_{-1}^{3}}{\mathbf{M}_{-3}}$ (8)

The obtained M_{-1} and M_{-3} moments decreases with the increasing NiO contain in NiO:Fe₂O₃ thin films as listed in TABLE 1.

CONCLUSION

Undoped and NiO doped Fe_2O_3 thin films were obtained by chemical spray pyrolysis method for different NiO contents. The Urbach energy decreased with increasing NiO content that lead to increase the energy gap, which increased from 2.53 eV before doping to 2.88 eV after 3% NiO-doping, also the same behavior of absorbance and the optical conductivity. While the real and imaginary dielectric constants and dispersion parameters such as E_d , E_x , M_{-1} , and M_{-3} are decreased with increasing NiO content in Fe_2O_3 thin films.

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